

6367255 MOTOROLA SC (DIODES/OPTO)

34C 38163 D

SILICON THYRISTOR DIE (continued)

7-25-17

CHIP NO. **MCR63-10** SERIES
LINE SOURCE — DTL0350



Device assembled from this die type are similar to the following device types:

- MCR63 Series
- MCR64 Series
- MCR65 Series

SCR — Silicon Controlled Rectifier

Voltage range from 25-800 volts available.

METALLIZATION —
 Top Al, Cr, Cu, Au
 Back Al, Cr, Cu, Au

CHIP THICKNESS 9.5 ± 0.5 mils

BONDING PAD SIZE:
 Anode 188 mils
 Cathode 188 mils
 Gate 46 mils
 Glassivation yes

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, See Note 1)

| Parameter | Test Conditions | Min | Max | Unit |
|-----------|--|-----|-----|-----------------|
| I_{DRM} | $V_D = \text{Rated } V_{DRM} (25-800 \text{ Vdc})$ | — | 50 | μAdc |
| I_{RRM} | $V_R = \text{Rated } V_{RRM}$ | — | 50 | μAdc |
| I_{GT} | $V_D = 12 \text{ Vdc}, R_L = 100 \Omega$ | — | 50 | mAdc |
| I_H | $V_D = 12 \text{ Vdc}, I_{TM} = 200 \text{ mAdc}$ | — | 60 | mAdc |
| V_{GT} | $V_D = 12 \text{ Vdc}, R_L = 100 \Omega$ | — | 1.5 | Vdc |

NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

Chip characteristics, including curves, are available from current Discrete Motorola Data.